Citations for Ion = He *, Target =* Si

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1956	Gobeli, G. W. **'Range-Energy Relation for Low-Energy Alpha Particles in Si, Ge and Insb'** ***Phys. Rev., 103, 275-78 (1956)*** *Comment : R. 0.70-4.45 MeV He -> Si, Ge, InSb, Al, Cu, Ag, Au.*	**1956-Gobe** 0056
1958	Garin, A. Faraggi, H. **'Parcours Des Alpha De 4.5 MeV Dans L'Uranium, L'Or, Le Zirconium Et Le Silicium.'** ***J. Phys. Radium, 19, 76-78 (1958)*** *Comment : R. 4.5 MeV He -> Si, Zr, Au, U. Ranges From He-Particle Emission From Uranium Alloys.*	**1958-Gari** 0773
1965	Sattler, A. R. **'Ionization Produced by Energetic Silicon Atoms Within a Silicon Lattice'** ***Phys. Rev. A, 138, 1815-21 (1965)*** *Comment : S. 21.2 - 3139 keV Si -> Si*	**1965-Satt** 0216
1966	Maccabee, H. D. Raju, M. R. Tobias, C. A. **'Fluctuations of Energy Loss in Semiconductor Detectors'** ***IEEE Trans. Nucl. Sci., NS-13, No. 6, 176-79 (1966)*** *Comment : dS. 730 MeV H, 910 MeV He -> Si*	**1966-Macc** 0730
1968	Maccabee, H. D. Raju, M. R. Tobias, C. H. **'Fluctuations of Energy Loss by Heavy Charged Particles in Thin Absorbers'** ***Phys. Rev., 165, 469-74 (1968)*** *Comment : dS. 45, 730 MeV H, 910 MeV He, 370 MeV Pi- -> Si*	**1968-Macc** 0314
1970	Avdeichikov, V. V. Gridnev, G. F. Lozhkin, O. V. Perfilov, N. A. **'The Limiting Energy Resolution of Thin De/Dx Detectors for 5-9 MeV Alpha Particles'** ***Bull. Acad. Sci. USSR Phys. Ser., 34, No. 1, 190-96 (1970)*** *Comment : dS. 5-8.7 MeV He -> Si*	**1970-Avde** 0711
1971	DellaMea, G. Drigo, A. V. LoRusso, S. Mazzoldi, P. Bentini, G. G. **'Energy Loss of H, D, and 4He Ions Channeled through Thin Single Crystals of Silicon'** ***Phys. Rev. Letters, 27, 1194-96 (1971)*** *Comment : S. 0.9-5.0 MeV H, D, He -> Si Cryst. And Amorph.*	**1971-Dell** 0132
1971	Thompson, D. A. Mackintosh, W. D. **'Stopping Cross Sections for 0.3 - 1.7 MeV Helium Ions in Silicon and Silicion Dioxide.'** ***J. Appl. Phys., 42, 3969-76 (1971)*** *Comment : S. 0.3-L.7 MeV He -> Si, SiO2*	**1971-Thom** 0492

1972
DellaMea, G. Drigo, A. V. LoRusso, S. Mazzoldi, P. Bentini, G. G.
'Transmission Energy Loss of Light Channeled Particles in Thin Silicon Single Crystals'
Rad. Effects, 13, 115-19 (1972)
Comment : S,dS. 0.9-5.0 MeV P, D, He -> Si (Cryst.)
1972-Dell2
0480

1972
Eisen, F. H. Clark, G. J. Bottiger, J. Poate, J. M.
'Stopping Power of Energetic Helium Ions Transmitted through Thin Silicon Crystals in Channeling and Random Directions'
Rad. Effects, 13, 93-100 (1972)
Comment : S,dS. 0.1-18 MeV He -> Si (Cryst.). Chan. And Random.
1972-Eise
0482

1973
Chu, W. K. Ziegler, J. F. Mitchell, I. V. Mackintosh, W. D.
'Energy-Loss Measurements of 4He Ions in Heavy Metals'
Appl. Phys. Letters, 22, 437-39 (1973)
Comment : S. 2.0 MeV He -> Al, Si, V, Fe, Co, Ni, Cu, In, Ge, Mo, Sb, Te, Gd, Hf, Ta, W, Ir, Pt, Au, Pb
1973-Chu 3
0124

1973
Feng, J. S. -Y. Chu, W. K. Nicolet, M. -A. Mayer, J. W.
'Relative Measurements of Stopping Cross Section Factors by Back-Scattering'
Thin Solid Films, 19, 195-204 (1973)
Comment : S (1-2 MeV) He -> Au, Ag, Cu, Al, Si. Relative Stopping
1973-Feng
0503

1973
Lin, W. K. Olson, H. G. Powers, D.
'Alpha-Particle Stopping Cross Sections of Silicon and Germanium'
J. Appl. Phys., 44, 3631-34 (1973)
Comment : S. 0.3-2.0 MeV He -> Si, Ge (Amorph.)
1973-Lin
0497

1973
Sellers, B. Hanser, A. Kelley, J. G.
'Energy Loss and Stopping Power Measurements Between 2 and 10 MeVamu for 3He and 4He in Silicon.'
Phys. Rev. B, 8, 98-102 (1973)
Comment : S. 6-30 MeV 3He, 8-40 MeV 4He -> Si (Cryst.?)
1973-Sell
0484

1973
Ziegler, J. F. Brodsky, M. H.
'Specific Energy Loss of 4He Ions in Silicon (Amorphous, Polycrystalline, and Single Crystal)'
J. Appl. Phys., 44, 188-96 (1973)
Comment : S. 0.42-2.75 MeV He -> Si
1973-Zieg
0474

1974
Avdeichikov, V. V. Ganza, E. A. Lozhkin, O. V.
'Energy-Loss Fluctuation of Heavy Charged Particles in Silicon Absorbers'
Nucl. Inst. Methods, 118, 247-52 (1974)
Comment : dS. 7.7 MeV He, 255 MeV Ar -> Si
1974-Avde
0628

1974 — **1974-Bagl** — 1583
Baglin, J. E. E.   Ziegler, J. F.
'Tests of Bragg's Rule for Energy Loss of 4He Ions in Solid Compounds'
J. Appl. Phys., 45, 1413-1415 (1974)
Comment : S. He (2 MeV) -> Si, Rh, Hf, Al, W, C, and many compounds

1974 — **1974-Schm** — 0519
Schmid, K.   Fischer, G.   Muller, H.   Ryssel, H.
'Experimental Data About Dechanneling and Channel Stopping Power'
Rad. Effects, 23, 145-49 (1974)
Comment : S. 1 MeV He -> Si (Cryst.)

1975 — **1975-Bulg** — 0799
Bulgakov, Yu. V.   Nikolaev, V. S.   Shulga,   V. I.
'Impact-Parameter Dependence of Inelastic Energy Losses for He and N Ions Channeled in Si'
Phys. Stat. Sol. A, 31, 341-50 (1975)
Comment : S, dS. 1.3, 6.6 MeV He, 4.4 MeV N -> Si (Cryst.)

1975 — **1975-Schu** — 0516
Schuch, R.
'Blocking-Effekte Bei Transmission von Alpha-Teilchen Durch Germanium - und Siliziumkristalle'
Z. Physik A, 272, 61-66 (1975)
Comment : S. 8.8 MeV He -> Si, Ge (Cryst.)

1976 — **1976-Avde** — 0882
Avdeichikov, V. V.   Ganza, E. A.   Lozhkin, O. V.
'Energy Resolution of Thin Semiconductor Delta-E Detectors for Alpha Particles and Heavy Ions'
Nucl. Inst. Methods, 131, 61-68 (1976)
Comment : dS. (1-200 MeV) He, C, N, O, Ne, Ar -> Si

1976 — **1976-Grah** — 0871
Grahmann, G.   Kalbitzer, S.
'Nuclear and Electronic Stopping Powers of Low Energy Ions with Z <= 10 in Silicon'
Nucl. Inst. Methods, 132, 119-23 (1976)
Comment : S. 2-60 keV H, He, B, C, N, Ne -> Si

1976 — **1976-Hoff** — 1259
Hoffman, I.   Jager, E.   Muller-Jahreis, U.
'Z1-Dependence of Electronic Energy Straggling of Light Ions'
Rad. Effects, 31, 57 (1976)
Comment : dS. 2 <= Z1 <=10 (10-100 Kev) -> C, Si

1976 — **1976-Mats** — 0890
Matsumura, H.   Furukawa, S.
'Simple Formulation for Energy Straggling of Helium in Silicon'
Rad. Effects, 27, 245-46 (1976)
Comment : dS. 1-2 MeV He -> Si

1976 — **1976-Wilk** — 1051
Wilken, B.   Fritz, T. A.
'Energy Distribution Functions of Low Energy Ions in Silicon Absorbers Measured for Large Relative Energy Losses'
Nucl. Inst. Methods, 138, 331-343 (1976)
Comment : dS. 300 keV-1.5 MeV H, 3He -> Si

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1977	Holland, O. W. Appleton, B. R. **'Well-Channelled Ions with Greater-Than-Random Energy Loss Rates'** ***IEEE Proc. of 4th Intl. Conf. on Small Accelerators, Denton, Tex. (1977)*** *Comment : S. 1.0 MeV He -> Si <111>*	**1977-Holl** 1257
1977	Jarvis, O. N. Sherwood, A. C. Whitehead, C. Lucas, M. W. **'Stopping Power for Fast Channeled Alpha Particles in Silicon'** ***Phys. Rev. B, 16, 3880-3886 (1977)*** *Comment : S. 160 MeV He -> Si ([110], [111], And Random)*	**1977-Jarv** 1038
1977	Thompson, D. A. Robinson, J. E. Walker, R. S. **'Inelastic Stopping of Medium Energy Light Ions in Silicon'** ***Rad. Effects, 32, 169-175 (1977)*** *Comment : dS,R,dR. 10-80 keV H, He, Li, B, C, N, O, Ne -> Si*	**1977-Thom** 1076
1978	Bottiger, J. Jensen, P. S. Littmark, U. **'Depth Profiles of 3He Ions Implanted into Solids at Energies Between 20 and 60 keV'** ***J. Appl. Phys., 49, 965-970 (1978)*** *Comment : R, dR. 20-60 keV 3He -> C, Al, Si, V, Ni, Zr*	**1978-Bott2** 1091
1978	Jarvis, O. N. Sherwood, A. C. Whitehead, C. Lucas, M. W. **'Channeling of Fast Protons, Deuterons and Alpha Particles'** ***Preprint (1978)*** *Comment : S, R, dR. 160 keV He, 81.5 keV D, 158.5 keV H -> Si*	**1978-Jarv** 1148
1978	Oetzmann, H. Kalbitzer, S. **'4He Stopping Power Measurements by using Ion Implantation and Backscattering Techniques'** ***Intl. Conf. Ion Beam Modification of Materials, Budapest -d (1978)*** *Comment : S. 0.15-1 MeV He -> C, Ge, Si*	**1978-Oetz** 1134
1978	Rosendahl, E. W. Monkediek, J. **'Measurement of the Energy Loss of Non-Channeled Alpha-Particles in Transmission and Interpretation with the Aid of an Averaged Continuum Potential'** ***Z. Physik A, 285, 33-36 (1978)*** *Comment : S. 8.78 MeV He -> Si*	**1978-Rose** 1125
1979	Jarvis, O. N. Sherwood, A. C. Whitehead, C. Lucas, M. W. **'Channeling of Fast Protons, Deuterons, and Alpha Particles'** ***Phys. Rev. B, 19, 5559-5577 (1979)*** *Comment : S, R, dR. 160 keV He, 81.5 keV D, 158.5 keV H -> Si*	**1979-Jarv** 1199
1979	Santry, D. C. Werner, R. D. **'Thickness Measurements of Thin Foils using Alpha Particles from 148Gd and 241Am'** ***Nucl. Inst. Methods, 159, 523-527 (1979)*** *Comment : S, dS. 3.138 MeV - 5.486 MeV He -> Be, C, Al, Si, Ni, Ag, Au*	**1979-Sant3** 1350

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1980	Heibei, J. Voges, E. **'Refractive Index of Ion-Implanted Fused Silica'** ***Phys. Stat. Sol. B, 57, 609-618 (1980)*** *Comment : R, dR. 100 keV He, Ar -> Si*	**1980-Heib** 1345
1980	Josquin, W. J. M. J. **'The Oxidation Characteristics of Nitrogen-Implanted Silicon'** ***Rad. Effects, 47, 221-224, (1980)*** *Comment : R, dR. 250-800 keV H, H2, He, B, P -> Si*	**1980-Josq** 1331
1980	Oetzmann, H. Kalbitzer, S. **'He4-Stopping Power Measurements by using Ion Implantation and Backscattering Techniques'** ***Rad. Effects, 47, 73-80 (1980)*** *Comment : S, dS. 0-1E5 keV He -> C, Si, Ge*	**1980-Oetz** 1324
1980	Santry, D. C. Werner, R. D. **'Stopping Power Values of Be, C, Al and Si for 4He Ions'** ***Nucl. Inst. Methods, 178, 523-530 (1980)*** *Comment : S. He (0.2-2.0 MeV) -> Be, C, Al, Si*	**1980-Sant2** 1407
1980	Sofield, C. J. Cowern, N. E. B. Freeman, J. M. **'Charge-Exchange Effects in Energy-Loss Straggling'** ***Nucl. Inst. Methods, 170, 221-225 (1980)*** *Comment : R, dR. 0-50 MeV Atomic Numbers 1-16 -> Al*	**1980-Sofi** 1378
1981	Pearce, J. D. Hart, R. R. **'Stopping Power Measurements in the 20-150 keV Region using Thick Target Backscattering: H and He on C, Si and Au'** ***J. Appl. Phys., 52, 5056 (1981)*** *Comment : S. H, He (20-150 keV) -> C, Si, Au*	**1981-Pear** 1736
1981	Santry, D. C. Werner, R. D. **'Stopping Power Values of C, Al, Si, Ni, Ag and Au for 3He Ions'** ***Nucl. Inst. Methods, 185, 517-521 (1981)*** *Comment : S. He3 (200-2000 keV) -> C, Al, Si, Ni, Ag, Au*	**1981-Sant2** 1449
1984	Santry, D. C. Werner, R. D. **'Stopping Powers of C, Al, Si, Ti, Ni, Ag, Au and Mylar using Radioactive Alpha Sources'** ***Nucl. Inst. Methods, B1, 13 (1984)*** *Comment : S. He (2-7 MeV) -> > C, Al, Si, Ti, Ni, Ag, Au, Mylar*	**1984-Sant** 1757
1986	Gnaser, H. Bay, H. L. Hofer, W. **'Depth Distributions of Low Energy He Implanted in Solids'** ***Nucl. Inst. Methods, B15, 49-53 (1986)*** *Comment : R, dR. He (0.25-80 keV) -> Si*	**1986-Gnas** 1523

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1987	Fink, D. Biersack, J. P. Stadele, M. Cheng, V. K. **'Range Profiles of Helium in Solids'** ***Rad. Effects, 104, 1-42 (1987)*** *Comment : R. He-3 (50-1500 keV) -> Be, C, Mg, Al, Si, Ti, V, Mn, Fe, Ca, Ni, Cu, Zn, Ge, Zr, Nb, Mo, Ag, Cd, In, Sn, Sb, Tb, Dy, Er, Ta, W, Ir, Pt, Au, Pb, Bi, SiC, MnO2*	**1987-Fink** 1645
1988	Yamaguchi, S. Takahiro, K. Nakajima, H. Fujino, Y. Sagara, S. **'Energy Loss of He Ions in H-Implanted Materials'** ***Nucl. Inst. Methods, B33, 163-167 (1988)*** *Comment : S. He (1.5 MeV) -> Be, Si, Al (doped with H)*	**1988-Yama** 1962
1993	Narumi, K. Fujii, Y. Kishine, K. Fujiwara, S. Kimura, K. **'Energy Losses of 12-32 keV H, He and N Ions at Glancing Angle Scattering from Clean Surfaces of Silicon Crystals'** ***J. Phys. Soc. Jap., 62, 1603-1611 (1993)*** *Comment : S. H, He, N (12-32 keV) -> Si Surface scattering effects*	**1993-Naru** 2054
1993	Nieman, D. Oberschachtsiek, P. Kalbitzer, S. Zeindl, H. P. **'Energy Loss and Straggling of MeV He-4 Ions in a Si/Sb Multilayer Target'** ***Nucl. Inst. Methods, B80/81, 37-40 (1993)*** *Comment : S, dS. He (0.1-4.0 MeV) -> Si/Sb Layers*	**1993-Niem** 1868
1995	Dos Santos, J. H. R. Grande, P. L. Boudinov, H. Behar, M. Stoll, R. **'Electronic Stopping Power of <100> Axial Channelled He Ions in Si Crystals'** ***Nucl. Inst. Methods, B106, 51-54 (1995)*** *Comment : S. He (0.2-4.5 MeV) -> Si*	**1995-Dos** 1832
1996	Gelfort, S. Kerkow, H. Stolle, R. Petukhov, V. P. Romanowski, E. A. **'Angular Dependence of the Electronic Energy Loss for Low Energy Heavy Ions under Channeling Conditions'** ***Nucl. Inst. Methods, B115, 315-318 (1996)*** *Comment : S. Channeling of ions He to Kr in Si <110>*	**1996-Gelf** 1814
1996	Misdaq, M. A. Elassali, R. **'Average Stopping Powers for Channeled Ions using Calculational and Experimental Methods'** ***Nucl. Inst. Methods, 119, 325-330 (1996)*** *Comment : S. Light ions -> Si, GaAs (channeled)*	**1996-Misd** 0964
1996	Niemann, D. Kinac, G. Kalbitzer, S. **'Stopping Power of H, He and N in Si in the Energy Range of 0.02-1.0 MeV/amu'** ***Nucl. Inst. Methods, 118, 11-18 (1996)*** *Comment : S. H, He, N (.02-1.0 MeV/amu) -> Si*	**1996-Niem** 1101

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
2000	Hoshino, Y. Okazawa, T. Nishii, T. Nishimura, T. Kido, Y. **'Correction of Ziegler's Stopping Powers of Al, Si and their Oxides for MeV He Ions'** ***Nucl. Inst. Methods, B171, 409-413 (2000)***	**2000-Hosh** 2344
Comment :	*S. He (1.1 - 2.6 MeV) -> Al, Si*	